CY7C1021CV26

1-Mbit (64K x 16) Static RAM

Features

- **Temperature Range**
  - **— Automotive: –40°C to 125°C**
- **High speed**
  - **— t_{AA} = 15 ns**
- **Optimized voltage range: 2.5V–2.7V**
- **Low active power: 360 mW (max.)**
- **Automatic power-down when deselected**
- **Independent control of upper and lower bits**
- **CMOS for optimum speed/power**
- **Package offered: 44-pin TSOP II**

Functional Description

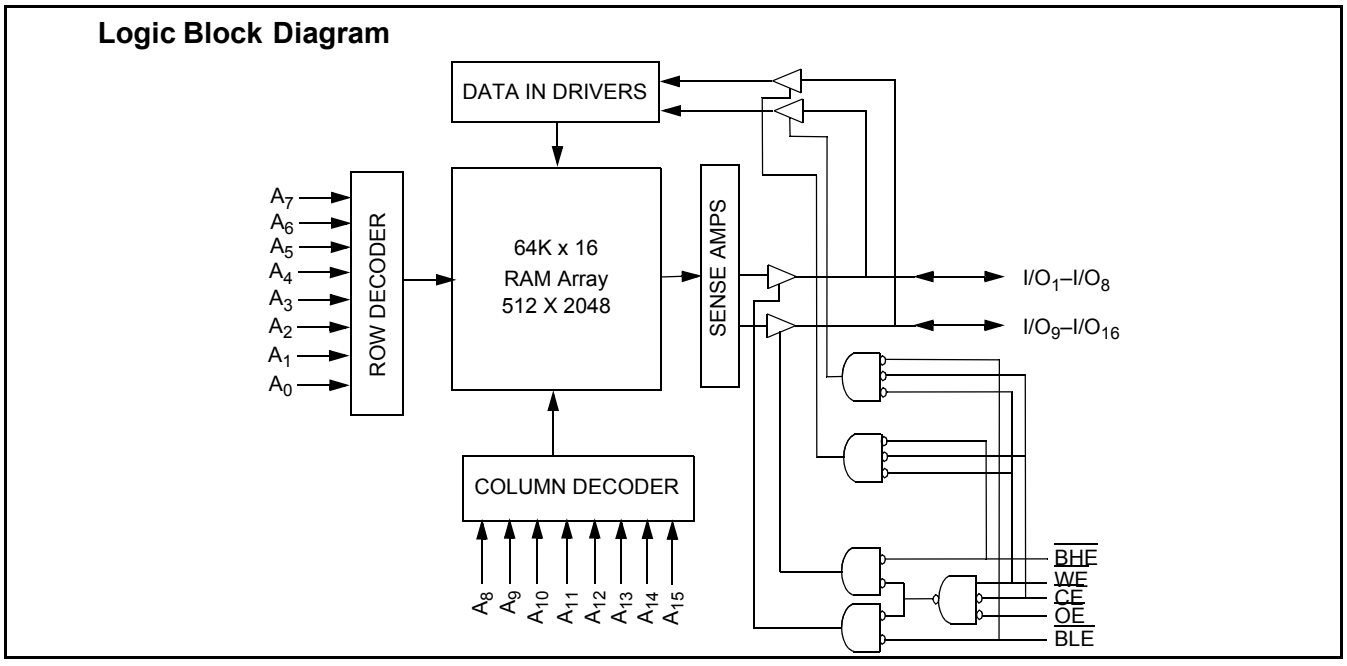
The CY7C1021CV26 is a high-performance CMOS static RAM organized as 65,536 words by 16 bits. This device has an automatic power-down feature that significantly reduces power consumption when deselected.

Writing to the device is accomplished by taking Chip Enable (CE) and Write Enable (WE) inputs LOW. If Byte Low Enable (BLE) is LOW, then data from I/O pins (I/O_1 through I/O_8), is written into the location specified on the address pins (A_0 through A_{15}). If Byte High Enable (BHE) is LOW, then data from I/O pins (I/O_9 through I/O_{16}) is written into the location specified on the address pins (A_0 through A_{15}).

Reading from the device is accomplished by taking Chip Enable (CE) and Output Enable (OE) LOW while forcing the Write Enable (WE) HIGH. If Byte Low Enable (BLE) is LOW, then data from the memory location specified by the address pins will appear on I/O_1 to I/O_8. If Byte High Enable (BHE) is LOW, then data from memory will appear on I/O_9 to I/O_{16}. See the truth table at the end of this data sheet for a complete description of Read and Write modes.

The input/output pins (I/O_1 through I/O_{16}) are placed in a high-impedance state when the device is deselected (CE HIGH), the outputs are disabled (OE HIGH), the BHE and BLE are disabled (BHE, BLE HIGH), or during a Write operation (CE LOW, and WE LOW).

Logic Block Diagram



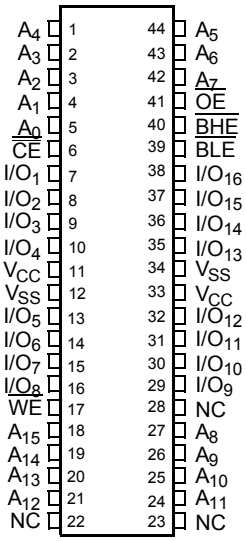
Selection Guide

	CY7C1021CV26-15
Maximum Access Time (ns)	15
Maximum Operating Current (mA)	80
Maximum CMOS Standby Current (mA)	10

Note:
1. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC(typ.)}$, $T_A = 25°C$.

Pin Configuration

TSOP II -Top View



Pin Definitions

Pin Name	Pin Number	I/O Type	Description
A_0–A_{15}	1–5, 18–21, 24–27, 42–44	Input	**Address Inputs used to select one of the address locations.**
I/O_1–I/O_{16}	7–10, 13–16, 29–32, 35–38	Input/Output	**Bidirectional Data I/O lines**. Used as input or output lines depending on operation.
NC	22, 23, 28	No Connect	**No Connects**. This pin is not connected to the die.
WE	17	Input/Control	**Write Enable Input, active LOW**. When selected LOW, a Write is conducted. When selected HIGH, a Read is conducted.
CE	6	Input/Control	**Chip Enable Input, active LOW**. When LOW, selects the chip. When HIGH, deselects the chip.
$\overline{BHE}$, $\overline{BLE}$	39, 40	Input/Control	**Byte Write Select Inputs, active LOW**. $\overline{BLE}$ controls I/O_8–I/O_1, $\overline{BHE}$ controls I/O_{16}–I/O_9.
OE	41	Input/Control	**Output Enable, active LOW**. Controls the direction of the I/O pins. When LOW, the I/O pins are allowed to behave as outputs. When deasserted HIGH, I/O pins are three-stated, and act as input data pins.
V_{SS}	12, 34	Ground	**Ground for the device**. Should be connected to ground of the system.
V_{CC}	11, 33	Power Supply	**Power Supply inputs to the device.**

Note:
2. NC pins are not connected on the die.

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature ..... –65°C to +150°C

Ambient Temperature with Power Applied ..... –55°C to +125°C

Supply Voltage on V_{CC} to Relative GND[3] .... –0.5V to +4.6V

DC Voltage Applied to Outputs in High-Z State[3] ..... –0.5V to V_{CC}+0.5V

DC Input Voltage[3] ..... –0.5V to V_{CC} + 0.5V

Current into Outputs (LOW)..... 20 mA

Static Discharge Voltage..... >2001V (per MIL-STD-883, Method 3015)

Latch-up Current..... >200 mA

Operating Range

Range	Ambient Temperature	V_{CC}
Automotive	–40°C to +125°C	2.5V–2.7V

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	CY7C1021CV26-15		Unit
			Min.	Max.	
V_{OH}	Output HIGH Voltage	V_{CC} = Min., I_{OH} = –1.0 mA	2.3		V
V_{OL}	Output LOW Voltage	V_{CC} = Min., I_{OL} = 1.0 mA		0.4	V
V_{IH}	Input HIGH Voltage		2.0	V_{CC} + 0.3	V
V_{IL}	Input LOW Voltage[3]		–0.3	0.8	V
I_{IX}	Input Load Current	GND ≤ V_I ≤ V_{CC}	–3	+3	μA
I_{OZ}	Output Leakage Current	GND ≤ V_I ≤ V_{CC}, Output Disabled	–3	+3	μA
I_{OS}	Output Short Circuit Current[4]	V_{CC} = Max., V_{OUT} = GND		–300	mA
I_{CC}	V_{CC} Operating Supply Current	V_{CC} = Max., I_{OUT} = 0 mA, f = f_{MAX} = $1/t_{RC}$		80	mA
I_{SB1}	Automatic CE Power-Down Current —TTL Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{IH} V_{IN} ≥ V_{IH} or V_{IN} ≤ V_{IL}, f = f_{MAX}		15	mA
I_{SB2}	Automatic CE Power-Down Current —CMOS Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{CC} – 0.3V, V_{IN} ≥ V_{CC} – 0.3V, or V_{IN} ≤ 0.3V, f = 0		10	mA

Capacitance[5]

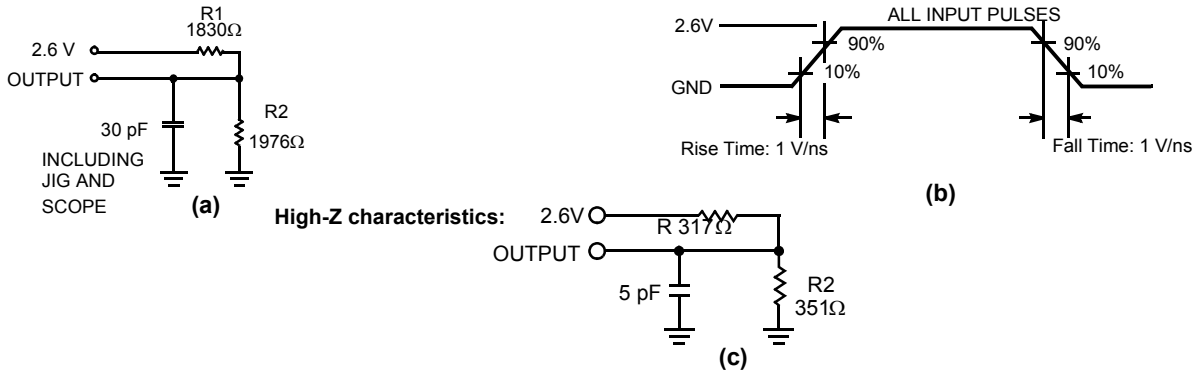
Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = 2.6V	8	pF
C_{OUT}	Output Capacitance		8	pF

Thermal Resistance[5]

Parameter	Description	Test Conditions	44-lead TSOP-II	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)[5]	Still Air, soldered on a 3 × 4.5 inch, two-layer printed circuit board	76.92	°C/W
Θ_{JC}	Thermal Resistance (Junction to Case)[5]		15.86	°C/W

Notes:
3. V_{IL} (min.) = –2.0V and V_{IH}(max) = V_{CC} + 0.5V for pulse durations of less than 20 ns.
4. Not more than one output should be shorted at one time. Duration of the short circuit should not exceed 30 seconds.
5. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms[6]



Switching Characteristics Over the Operating Range[7]

Parameter	Description	CY7C1021CV26-15		Unit
		Min.	Max.	
Read Cycle				
t_{RC}	Read Cycle Time	15		ns
t_{AA}	Address to Data Valid		15	ns
t_{OHA}	Data Hold from Address Change	3		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		15	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		7	ns
t_{LZOE}	$\overline{OE}$ LOW to Low-Z[8]	0		ns
t_{HZOE}	$\overline{OE}$ HIGH to High-Z[8, 9]		7	ns
t_{LZCE}	$\overline{CE}$ LOW to Low-Z[8]	3		ns
t_{HZCE}	$\overline{CE}$ HIGH to High-Z[8, 9]		7	ns
t_{PU}[10]	$\overline{CE}$ LOW to Power-Up	0		ns
t_{PD}[10]	$\overline{CE}$ HIGH to Power-Down		15	ns
t_{DBE}	Byte Enable to Data Valid		7	ns
t_{LZBE}	Byte Enable to Low-Z	0		ns
t_{HZBE}	Byte Disable to High-Z		7	ns
Write Cycle[11]				
t_{WC}	Write Cycle Time	15		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	10		ns
t_{AW}	Address Set-Up to Write End	10		ns
t_{HA}	Address Hold from Write End	0		ns
t_{SA}	Address Set-Up to Write Start	0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	10		ns
t_{SD}	Data Set-Up to Write End	8		ns
t_{HD}	Data Hold from Write End	0		ns

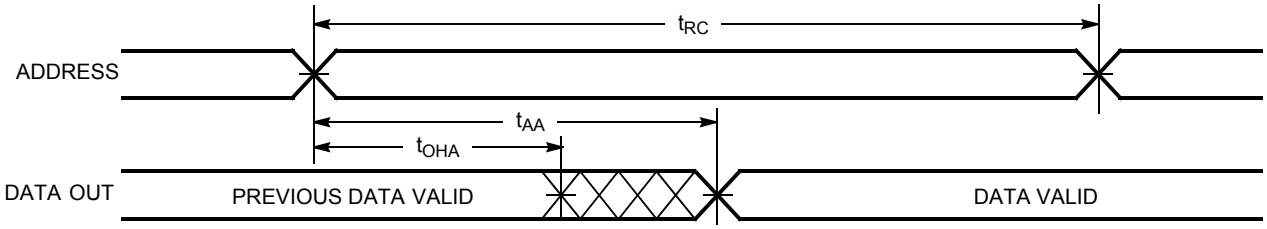
Notes:
6. AC characteristics (except High-Z) are tested using the Thevenin load shown in Figure (a). High-Z characteristics are tested for all speeds using the test load shown in Figure (c).
7. Test conditions assume signal transition time of 2.6 ns or less, timing reference levels of 1.3V, input pulse levels of 0 to 2.6V.
8. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
9. t_{HZOE}, t_{HZBE}, t_{HZCE}, and t_{HZWE} are specified with a load capacitance of 5 pF as in part (d) of AC Test Loads. Transition is measured ±500 mV from steady-state voltage.
10. This parameter is guaranteed by design and is not tested.
11. The internal Write time of the memory is defined by the overlap of $\overline{CE}$ LOW, $\overline{WE}$ LOW and $\overline{BHE}$/$\overline{BLE}$ LOW. $\overline{CE}$, $\overline{WE}$ and $\overline{BHE}$/$\overline{BLE}$ must be LOW to initiate a Write, and the transition of these signals can terminate the Write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the Write.

Switching Characteristics Over the Operating Range[7] (continued)

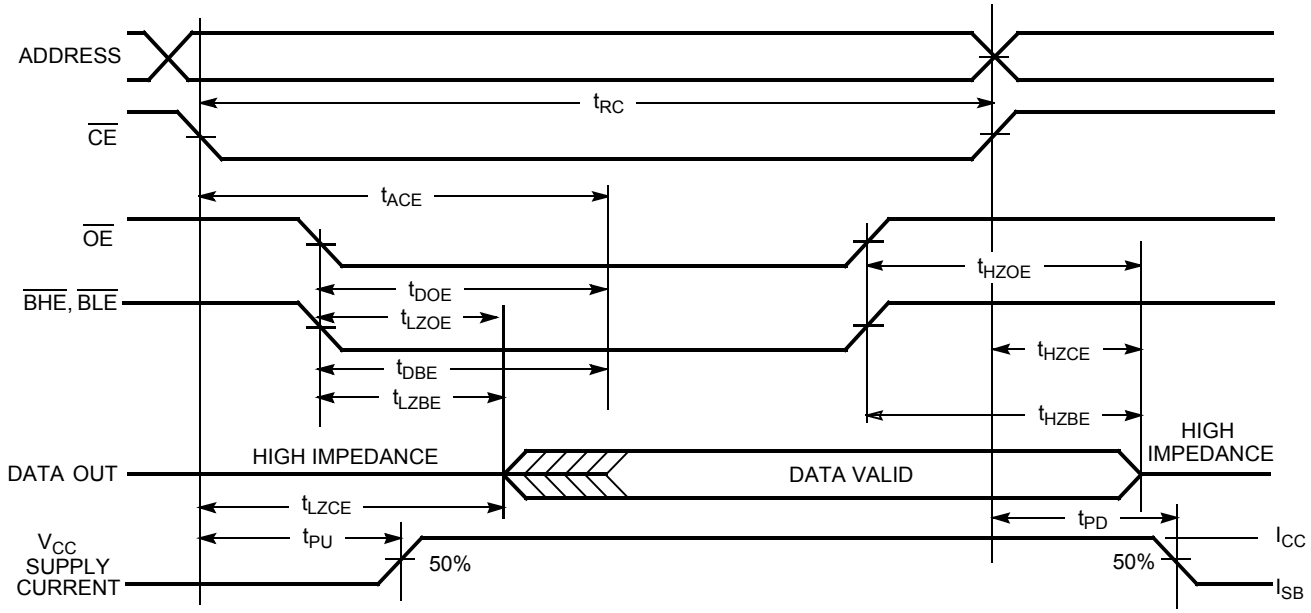
Parameter	Description	CY7C1021CV26-15		Unit
		Min.	Max.	
t_{LZWE}	$\overline{WE}$ HIGH to Low-Z[8]	3		ns
t_{HZWE}	$\overline{WE}$ LOW to High-Z[8, 9]		7	ns
t_{BW}	Byte Enable to End of Write	9		ns

Switching Waveforms

Read Cycle No. 1[12, 13]



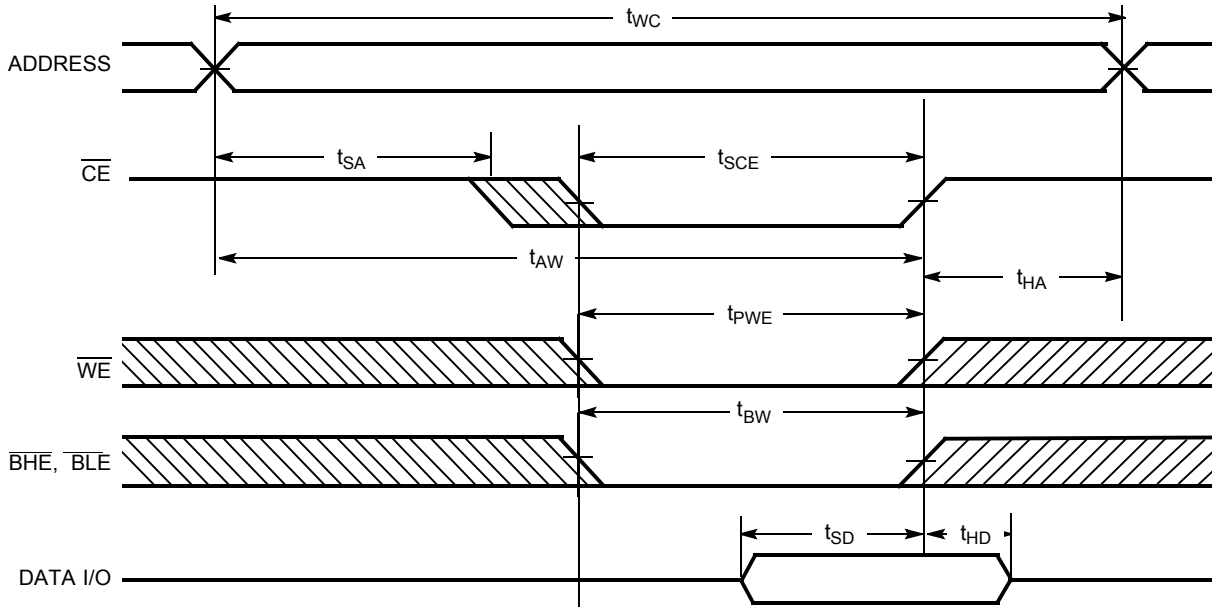
Read Cycle No. 2 ($\overline{OE}$ Controlled)[13, 14]



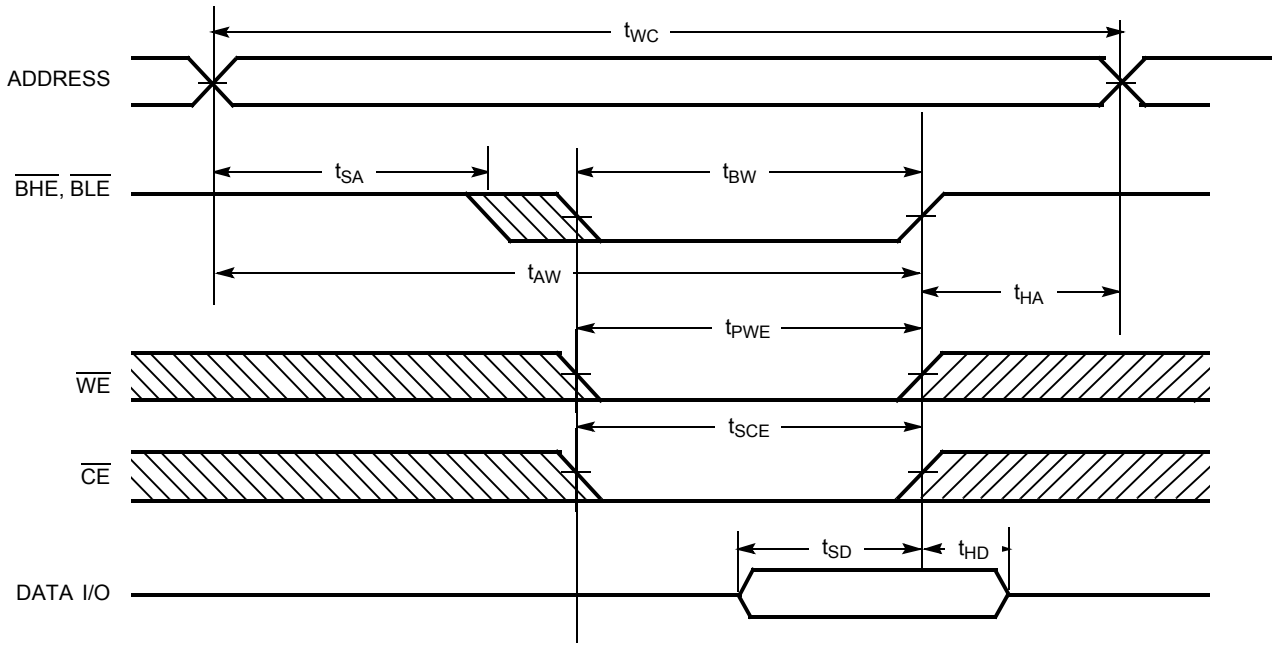
Notes:
12. Device is continuously selected. $\overline{OE}$, $\overline{CE}$, $\overline{BHE}$ and/or $\overline{BLE}$ = V_{IL}.
13. $\overline{WE}$ is HIGH for Read cycle.
14. Address valid prior to or coincident with $\overline{CE}$ transition LOW.

Switching Waveforms (continued)

Write Cycle No. 1 ($\overline{CE}$ Controlled)[15, 16]



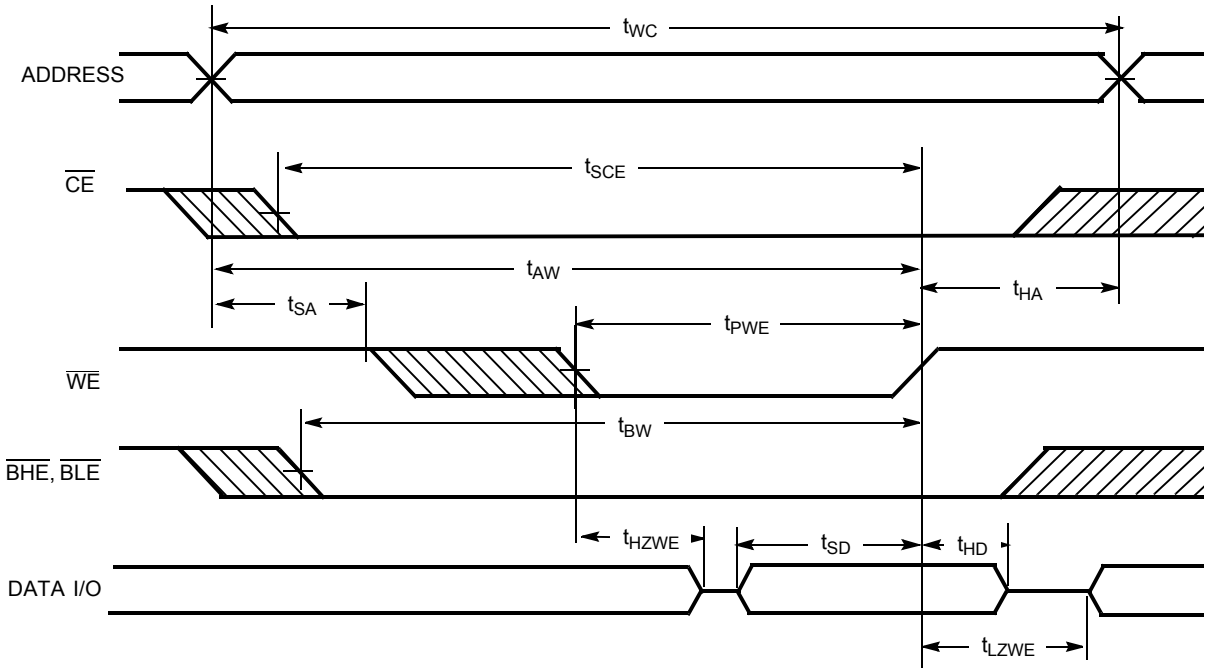
Write Cycle No. 2 ($\overline{BLE}$ or $\overline{BHE}$ Controlled)



Notes:
15. Data I/O is high-impedance if $\overline{OE}$ or $\overline{BHE}$ and/or $\overline{BLE}$= V_{IH}.
16. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ going HIGH, the output remains in a high-impedance state.

Switching Waveforms (continued)

Write Cycle No. 3 ($\overline{WE}$ Controlled, LOW)



Truth Table

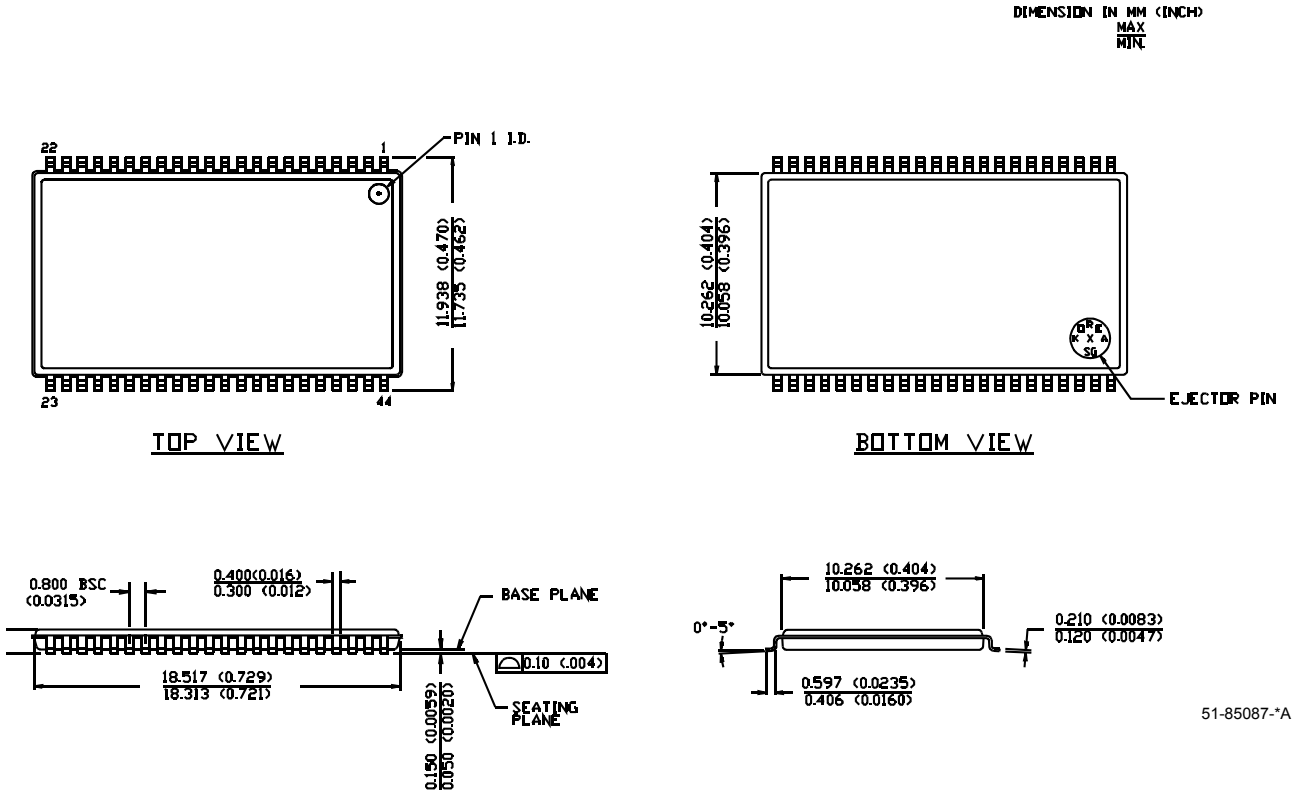
$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	$\overline{BLE}$	$\overline{BHE}$	I/O_1–I/O_8	I/O_9–I/O_{16}	Mode	Power
H	X	X	X	X	High-Z	High-Z	Power-down	Standby (I_{SB})
L	L	H	L	L	Data Out	Data Out	Read – All bits	Active (I_{CC})
			L	H	Data Out	High-Z	Read – Lower bits only	Active (I_{CC})
			H	L	High-Z	Data Out	Read – Upper bits only	Active (I_{CC})
L	X	L	L	L	Data In	Data In	Write – All bits	Active (I_{CC})
			L	H	Data In	High-Z	Write – Lower bits only	Active (I_{CC})
			H	L	High-Z	Data In	Write – Upper bits only	Active (I_{CC})
L	H	H	X	X	High-Z	High-Z	Selected, Outputs Disabled	Active (I_{CC})
L	X	X	H	H	High-Z	High-Z	Selected, Outputs Disabled	Active (I_{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
15	CY7C1021CV26-15ZE	Z44	44-lead TSOP Type II	Automotive

Package Diagrams

44-pin TSOP II Z44



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Document History Page

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REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	238454	See ECN	RKF	New datasheet for Automotive